

IN THE SPECIFICATION

Please amend paragraph [0030] at page 11, line 3 as shown in the following replacement paragraph:

Next, in Fig. 5C, a patterning layer 510 is deposited over dielectric layer 508, where patterning layer 510 will be used to expose portions of the dielectric layer where microlenses or non-spherical lenses will be formed. Patterning layer 510 is a photosensitive dielectric material and is selected based on the type of patterning process used. For example, for a photolithography process, patterning layer 510 can be a spin-on photoresist or other photosensitive material. The desired pattern can then be formed on patterning layer 510 by exposure through a photomask. The photomask, if the photoresist is positive, may have an array of circular openings, where the circular openings correspond to locations of the microlenses to be formed. If the microlenses are to have different shapes and/or sizes, the individual openings of the photomask can be adjusted accordingly. Exposed portions of patterning layer 510 are then removed to expose portions 512 of dielectric layer 508 where microlenses or non-spherical lenses are to be formed, as shown in Fig. 5D. With an underlying sensor array, portions 512 correspond to individual sensor elements 504.

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